MC14106B

Hex Schmitt Trigger

The MC14106B hex Schmitt Trigger is constructed with MOS P−channel and N−channel enhancement mode devices in a single monolithic structure. These devices find primary use where low power dissipation and/or high noise immunity is desired. The MC14106B may be used in place of the MC14069UB hex inverter for enhanced noise immunity or to “square up” slowly changing waveforms.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

Features

- Increased Hysteresis Voltage Over the MC14584B
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low−power TTL Loads or One Low−power Schottky TTL Load Over the Rated Temperature Range
- Pin−for−Pin Replacement for CD40106B and MM74C14
- Can Be Used to Replace the MC14584B or MC14069UB
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 1)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: “D/DW” Packages: –7.0 mW/°C From 65°C To 125°C

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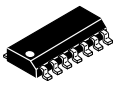
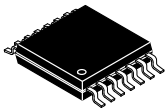
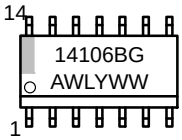


SOIC−14 NB
D SUFFIX
CASE 751A

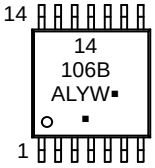


TSSOP−14
DT SUFFIX
CASE 948G

MARKING DIAGRAMS



SOIC−14 NB



TSSOP−14

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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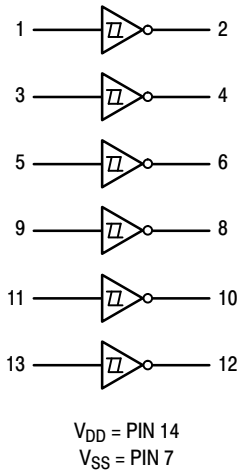


Figure 1. Logic Diagram

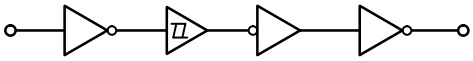


Figure 2. Equivalent Circuit Schematic (1/6 of Circuit Shown)

ORDERING INFORMATION

Device	Package	Shipping†
MC14106BDG	SOIC−14 NB (Pb−Free)	55 Units / Rail
NLV14106BDG*	SOIC−14 NB (Pb−Free)	55 Units / Rail
MC14106BDR2G	SOIC−14 NB (Pb−Free)	2500 / Tape & Reel
NLV14106BDR2G*	SOIC−14 NB (Pb−Free)	2500 / Tape & Reel
MC14106BDTR2G	TSSOP−14 (Pb−Free)	2500 / Tape & Reel
NLV14106BDTR2G*	TSSOP−14 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	−55°C Min	−55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD}	V_{OL}	5.0	−	0.05	−	0	0.05	−	0.05	Vdc
		10	−	0.05	−	0	0.05	−	0.05	
		15	−	0.05	−	0	0.05	−	0.05	
“1” Level V_{in} = 0	V_{OH}	5.0	4.95	−	4.95	5.0	−	4.95	−	Vdc
		10	9.95	−	9.95	10	−	9.95	−	
		15	14.95	−	14.95	15	−	14.95	−	
Hysteresis Voltage	V_H (5)	5.0	0.3	2.0	0.3	1.1	2.0	0.3	2.0	Vdc
		10	1.2	3.4	1.2	1.7	3.4	1.2	3.4	
		15	1.6	5.0	1.6	2.1	5.0	1.6	5.0	
Threshold Voltage Positive−Going	V_{T+}	5.0	2.2	3.6	2.2	2.9	3.6	2.2	3.6	Vdc
		10	4.6	7.1	4.6	5.9	7.1	4.6	7.1	
		15	6.8	10.8	6.8	8.8	10.8	6.8	10.8	
Negative−Going	V_{T-}	5.0	0.9	2.8	0.9	1.9	2.8	0.9	2.8	Vdc
		10	2.5	5.2	2.5	3.9	5.2	2.5	5.2	
		15	4.0	7.4	4.0	5.8	7.4	4.0	7.4	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	–3.0	−	–2.4	–4.2	−	–1.7	−	
(V_{OH} = 4.6 Vdc)		5.0	–0.64	−	–0.51	–0.88	−	–0.36	−	
(V_{OH} = 9.5 Vdc)		10	–1.6	−	–1.3	–2.25	−	–0.9	−	
(V_{OH} = 13.5 Vdc)		15	–4.2	−	–3.4	–8.8	−	–2.4	−	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	−	0.51	0.88	−	0.36	−	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	−	1.3	2.25	−	0.9	−	
(V_{OL} = 1.5 Vdc)		15	4.2	−	3.4	8.8	−	2.4	−	
Input Current	I_{in}	15	−	±0.1	−	±0.00001	±0.1	−	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	−	−	−	−	5.0	7.5	−	−	pF
Quiescent Current (Per Package)	I_{DD}	5.0	−	0.25	−	0.0005	0.25	−	7.5	μAdc
		10	−	0.5	−	0.0010	0.5	−	15	
		15	−	1.0	−	0.0015	1.0	−	30	
Total Supply Current (Notes 3 & 4) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0	I_T = (1.8 μA/kHz) f + I_{DD}							μAdc
		10	I_T = (3.6 μA/kHz) f + I_{DD}							
		15	I_T = (5.4 μA/kHz) f + I_{DD}							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:
   $I_T(C_L) = I_T(50\ pF) + (C_L – 50)$ Vfk where I_T is in μA (per package), C_L in pF, V = ($V_{DD} – V_{SS}$) in volts, f in kHz is input frequency, and k = 0.001.
5. $V_H = V_{T+} – V_{T-}$ (But maximum variation of V_H is specified as less that $V_{T+\ max} – V_{T-\ min}$).

SWITCHING CHARACTERISTICS (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}	5.0 10 15	– – –	100 50 40	200 100 80	ns
Output Fall Time	t_{THL}	5.0 10 15	– – –	100 50 40	200 100 80	ns
Propagation Delay Time	t_{PLH}, t_{PHL}	5.0 10 15	– – –	125 50 40	250 100 80	ns

6. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

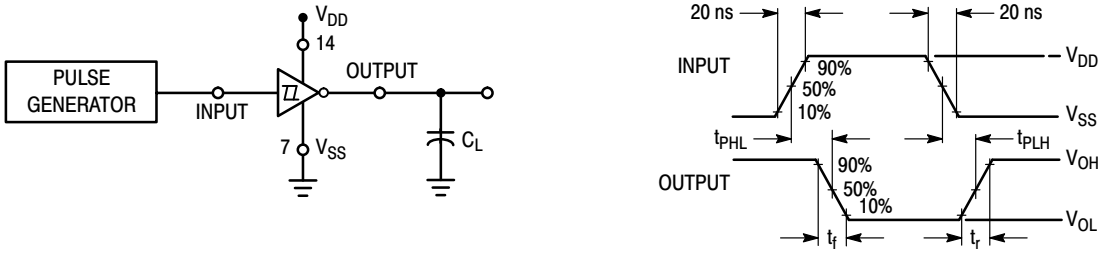


Figure 1. Switching Time Test Circuit and Waveforms

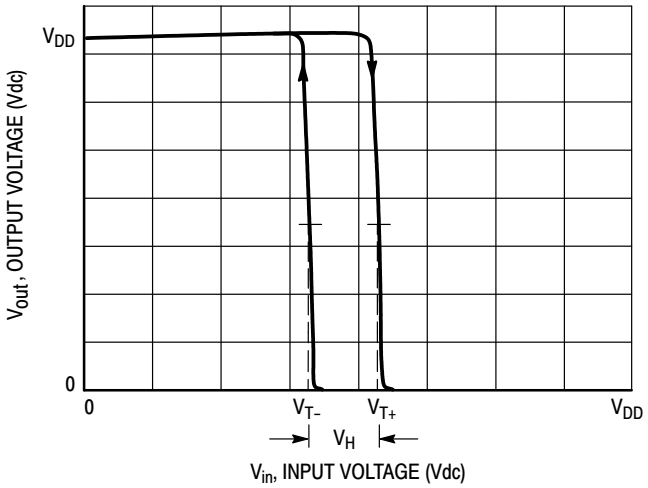
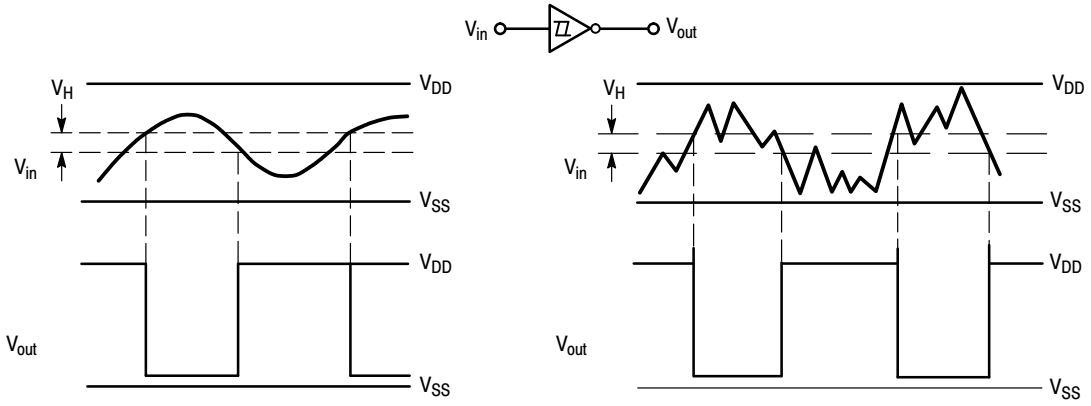


Figure 2. Typical Transfer Characteristics

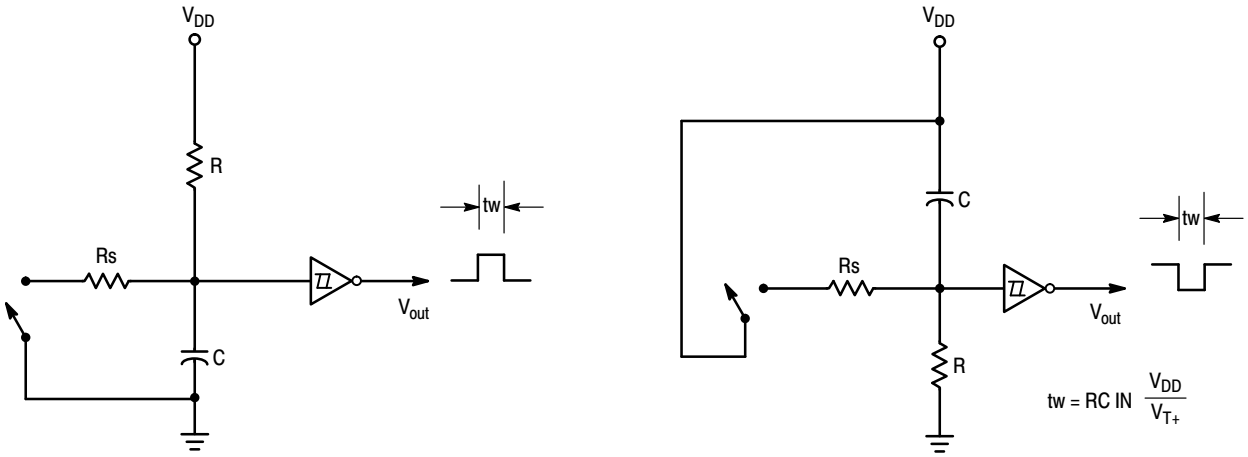
APPLICATIONS



(a) Schmitt Triggers will square up inputs with slow rise and fall times.

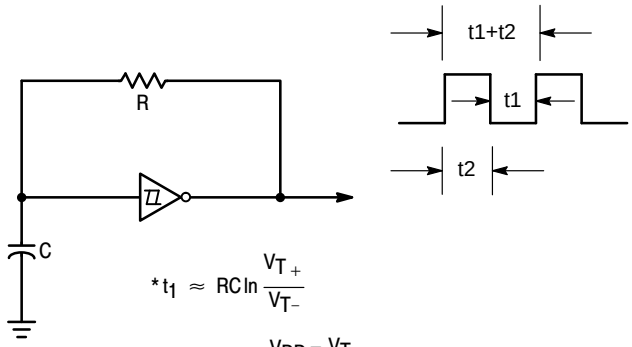
(b) A Schmitt trigger offers maximum noise immunity in gate applications.

Figure 3.



Useful as Pushbutton/Keyboard Debounce Circuit.

Figure 4. Monostable Multivibrator



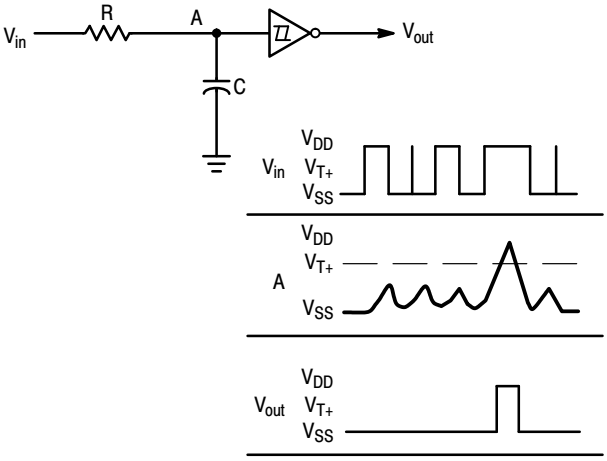
$$*t_1 \approx RC \ln \frac{V_{T+}}{V_{T-}}$$

$$*t_2 \approx RC \ln \frac{V_{DD} - V_{T-}}{V_{DD} - V_{T+}}$$

$$\frac{1}{f} \approx RC \ln \left[\left(\frac{V_{DD} - V_{T-}}{V_{DD} - V_{T+}} \right) \left(\frac{V_{T+}}{V_{T-}} \right) \right]$$

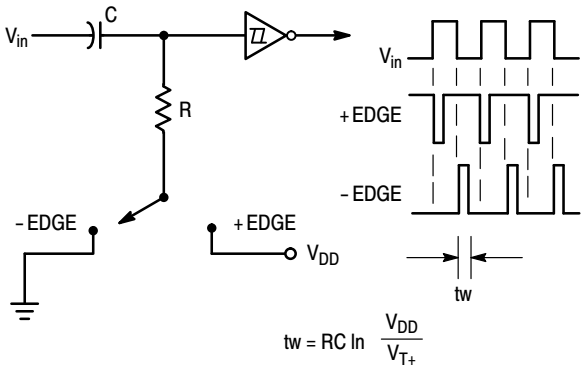
$*t_1 + t_2 \gg t_{PHL} + t_{PLH}$

Figure 5. Astable Multivibrator



Useful in discriminating against short pulse durations.

Figure 6. Integrator



$$tw = RC \ln \frac{V_{DD}}{V_{T+}}$$

Useful as an edge detector circuit.

Figure 7. Differentiator

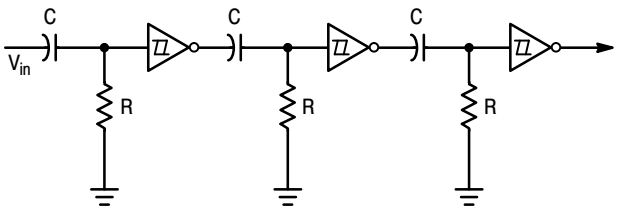
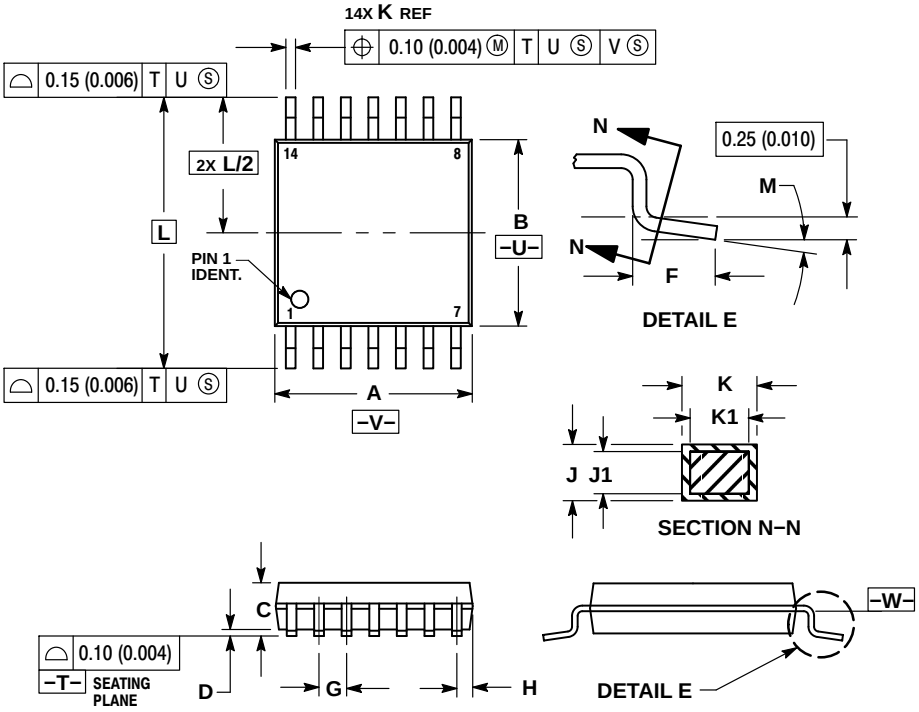


Figure 8. Positive Edge Time Delay Circuit

PACKAGE DIMENSIONS

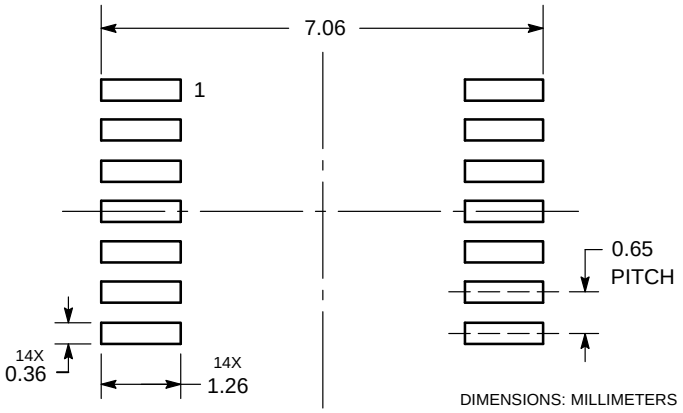
TSSOP−14
CASE 948G
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

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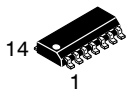
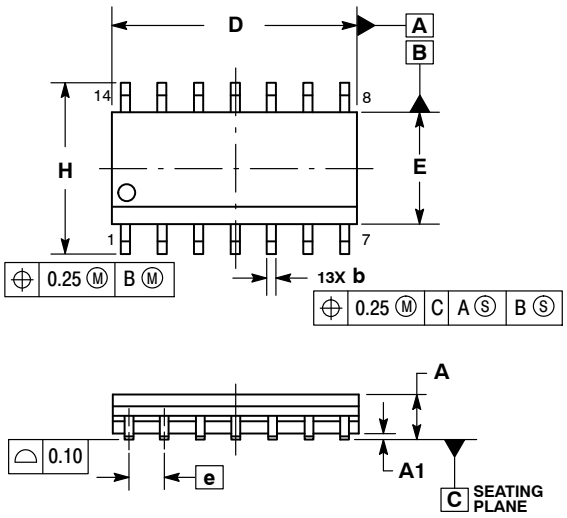
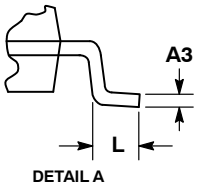


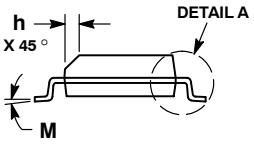
SCALE 1:1

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



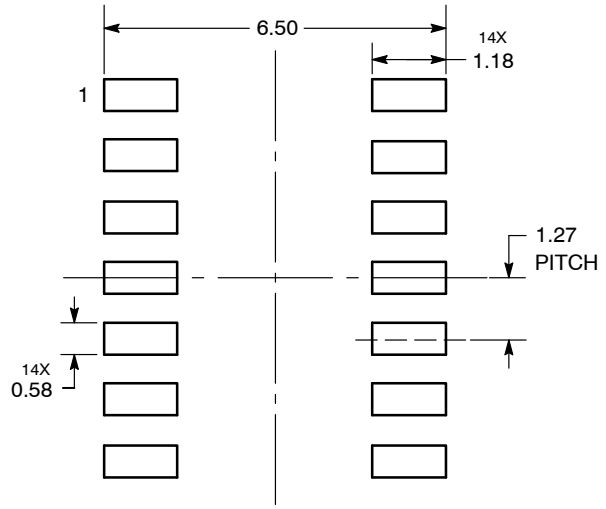




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

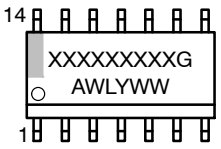
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC−14 NB		PAGE 1 OF 2

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SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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